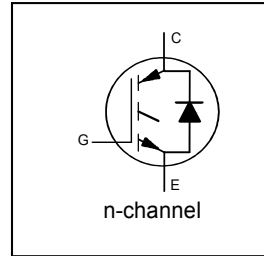
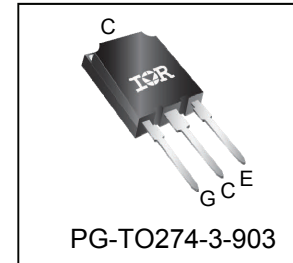


INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE
Features

- Low $V_{CE(on)}$ Trench IGBT Technology
- Low Switching Losses
- 6 μ s SCSOA
- Square RBSOA
- 100% of the parts tested for I_{LM} ①
- Positive $V_{CE(on)}$ Temperature Coefficient
- Soft Recovery Co-pak Diode
- Lead-Free, RoHS Compliant
- Automotive Qualified *



$V_{CES} = 600V$
 $I_C = 160A, T_C = 100^\circ C$
 $t_{sc} \geq 6\mu s, T_{J(MAX)} = 175^\circ C$
 $V_{CE(on) typ.} = 1.70V$



G	C	E
Gate	Collector	Emitter

Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for Applications in the Low to Mid-Range Frequencies
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGPS4070D0	PG-TO274-3-903	Tube	25	AUIRGPS4070D0

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	240⑤	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	160	
$I_{NOMINAL}$	Nominal Current	120	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$	360	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	480	
$I_{F NOMINAL}$	Diode Nominal Current ②	120⑤	
I_{FM}	Diode Maximum Forward Current ②	480	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	750	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	375	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (each IGBT) ④	—	0.20	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case (each Diode) ④	—	0.45	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	

* Qualification standards can be found at www.infineon.com

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 500μA ③
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.74	—	V/°C	V _{GE} = 0V, I _C = 5mA (25°C-175°C)
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	I _C = 120A, V _{GE} = 15V, T _J = 25°C
		—	2.0	—		I _C = 120A, V _{GE} = 15V, T _J = 150°C
		—	2.1	—		I _C = 120A, V _{GE} = 15V, T _J = 175°C
V _{GE(th)}	Gate Threshold Voltage	4.0	—	6.5	V	V _{CE} = V _{GE} , I _C = 5.6mA
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-16	—	mV/°C	V _{CE} = V _{GE} , I _C = 5.6mA (25°C-175°C)
g _{fe}	Forward Transconductance	—	87	—	S	V _{CE} = 50V, I _C = 120A
I _{CES}	Collector-to-Emitter Leakage Current	—	1.0	200	μA	V _{GE} = 0V, V _{CE} = 600V
		—	2.0	—	mA	V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C
V _{FM}	Diode Forward Voltage Drop	—	1.8	2.1	V	I _F = 120A
		—	1.9	—		I _F = 120A, T _J = 175°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q _g	Total Gate Charge (turn-on)	—	250	375	nC	I _C = 120A V _{GE} = 15V V _{CC} = 400V	
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	65	98			
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	100	150			
E _{on}	Turn-On Switching Loss	—	5.7	6.7	mJ	I _C = 120A, V _{CC} = 400V, V _{GE} = 15V R _G = 4.7Ω, L = 87μH, T _J = 25°C Energy losses include tail & diode reverse recovery	
E _{off}	Turn-Off Switching Loss	—	4.2	5.2			
E _{total}	Total Switching Loss	—	9.9	11.9			
t _{d(on)}	Turn-On delay time	—	40	60	ns		
t _r	Rise time	—	125	155			
t _{d(off)}	Turn-Off delay time	—	140	170			
t _f	Fall time	—	120	170			
E _{on}	Turn-On Switching Loss	—	6.4	—	mJ		I _C = 120A, V _{CC} = 400V, V _{GE} = 15V R _G = 4.7Ω, L = 87μH, T _J = 175°C Energy losses include tail & diode reverse recovery
E _{off}	Turn-Off Switching Loss	—	4.7	—			
E _{total}	Total Switching Loss	—	11.1	—			
t _{d(on)}	Turn-On delay time	—	40	—	ns		
t _r	Rise time	—	110	—			
t _{d(off)}	Turn-Off delay time	—	160	—			
t _f	Fall time	—	125	—			
C _{ies}	Input Capacitance	—	7600	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0Mhz	
C _{oes}	Output Capacitance	—	510	—			
C _{res}	Reverse Transfer Capacitance	—	230	—			
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 175°C, I _C = 480A V _{CC} = 480V, V _p ≤ 600V R _G = 4.7Ω, V _{GE} = +20V to 0V	
SCSOA	Short Circuit Safe Operating Area	6	—	—	μs	V _{CC} = 400V, V _p ≤ 600V R _G = 5.0Ω, V _{GE} = +15V to 0V	
E _{rec}	Reverse Recovery Energy of the Diode	—	1740	—	μJ	T _J = 175°C	
t _{rr}	Diode Reverse Recovery Time	—	210	—	ns	V _{CC} = 400V, I _F = 120A	
I _{rr}	Peak Reverse Recovery Current	—	45	—	A	V _{GE} = 15V, R _G = 4.7Ω, L = 87μH	

Notes:

- ① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 3.5μH, R_G = 47 Ω tested in production ILM ≤ 400A.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring V_{(BR)CES} safely.
- ④ R_θ is measured at T_J approximately 90°C.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package IGBT current limit is 195A. Package diode current limit is 120A. Note that current limitations arising from heating of the device leads may occur.